

Silicon NPN Power Transistors

2SC4544

DESCRIPTION

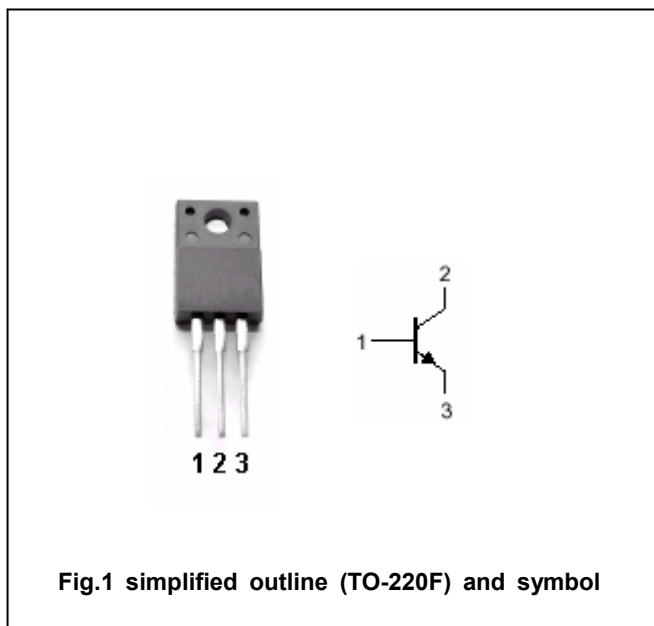
- With TO-220F package
- High Voltage

APPLICATIONS

- Color TV horizontal driver applications
- Color TV chroma output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		100	mA
I _B	Base current		50	mA
P _C	Collector power dissipation	T _a =25°C	2	W
		T _C =25°C	8	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =100μA; I _B =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA ; I _B =1m A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10mA ; I _B =1m A			1.0	V
h _{FE-1}	DC current gain	I _C =4mA ; V _{CE} =10V	20			
h _{FE-2}	DC current gain	I _C =20mA ; V _{CE} =10V	30		200	
I _{CBO}	Collector cut-off current	V _{CB} =240V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			1.0	μA
C _{OB}	Output capacitance	I _E =0; V _{CB} =20V; f=1MHz		3		pF
f _T	Transition frequency	I _C =20mA ; V _{CE} =10V	50	70		MHz

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PACKAGE OUTLINE

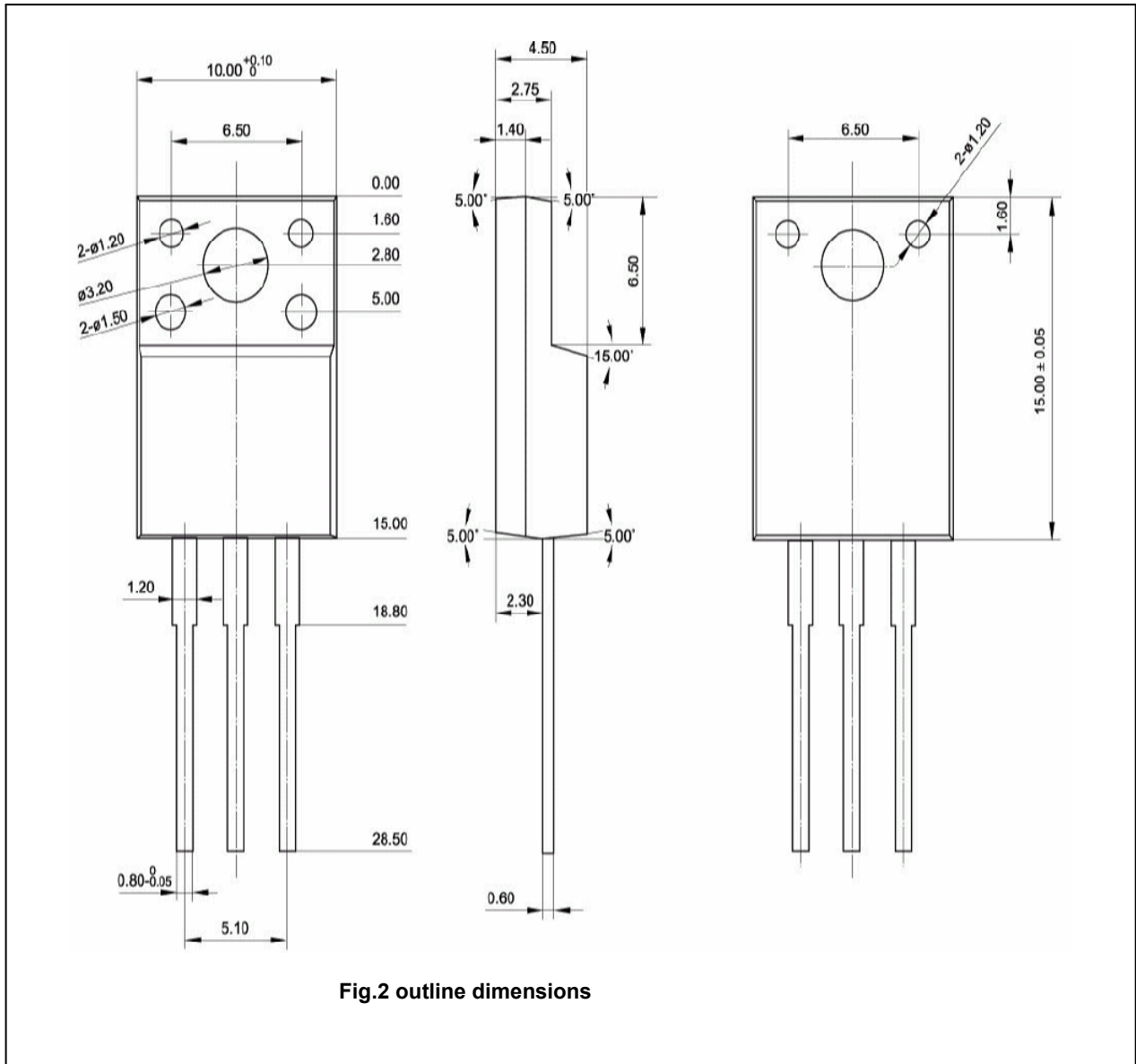


Fig.2 outline dimensions